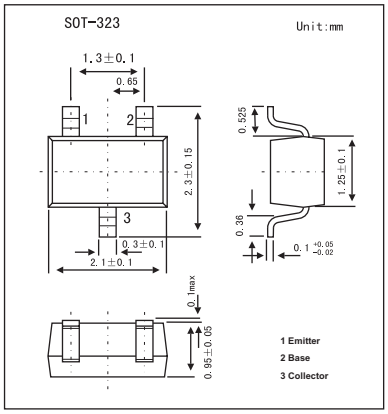
Silicon NPN Epitaxial

2SC4253



■ Features

- Good linearity of f_T.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	25	V
Emitter-base voltage	V_{EBO}	4	V
Collector current	I_C	50	mA
Base current	I_B	25	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = 30 V, I_E = 0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = 3 V, I_C = 0			0.1	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 1 mA, I_B = 0	25			V
DC current gain	h_{FE}	V_{CE} = 10 V, I_C = 10 mA	20	70	200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 15 mA, I_B = 1.5mA			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C = 15 mA, I_B = 1.5mA			1.5	V
Collector output capacitance	C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1MHz		1.1	1.6	pF
Collector-base time constant	$C_c.r_{bb}'$	V_{CB} = 10 V, I_C = 1mA, f = 30MHz			25	ps
Transition frequency	f_T	V_{CE} = 10 V, I_C = 10 mA	250	600		MHz

■ Marking

Marking	HH